

RAD-TOLERANT CLASS V, HIGH-SPEED PWM CONTROLLER

FEATURES

- QML-V Qualified, SMD 5962-87681
- Rad-Tolerant: 30 kRad (Si) TID (1)
- Compatible With Voltage- or Current-Mode Topologies
- Practical Operation Switching Frequencies to 1 MHz
- 50-ns Propagation Delay-to-Output
- High-Current Dual Totem Pole Outputs (1.5 A Peak)
- Wide Bandwidth Error Amplifier
- Fully Latched Logic With Double-Pulse Suppression
- Pulse-by-Pulse Current Limiting
- Soft Start/Maximum Duty-Cycle Control
- Undervoltage Lockout With Hysteresis
- Low Start-Up Current (1.1 mA)
- (1) Radiation tolerance is a typical value based upon initial device qualification with dose rate = 10 mrad/sec. Radiation Lot Acceptance Testing is available - contact factory for details.

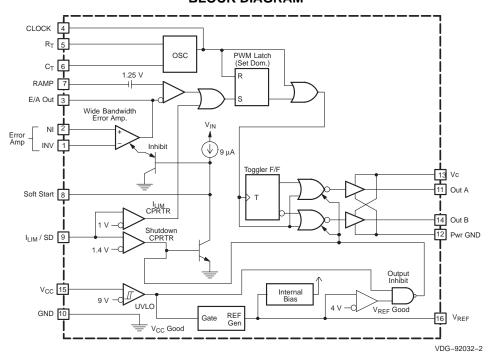
DESCRIPTION

The UC1825 PWM control device is optimized for high-frequency switched mode power supply applications. Particular care was given to minimizing propagation delays through the comparators and logic circuitry while maximizing bandwidth and slew rate of the error amplifier. This controller is designed for use in either current-mode or voltage mode systems with the capability for input voltage feed-forward.

Protection circuitry includes a current limit comparator with a 1-V threshold, a TTL compatible shutdown port, and a soft start pin which will double as a maximum duty-cycle clamp. The logic is fully latched to provide jitter-free operation and prohibit multiple pulses at an output. An undervoltage lockout section with 800 mV of hysteresis assures low start up current. During undervoltage lockout, the outputs are high impedance.

This device features totem pole outputs designed to source and sink high peak currents from capacitive loads, such as the gate of a power MOSFET. The on state is designed as a high level.

BLOCK DIAGRAM





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





This device has limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION(1)

T _A	PACKAGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–55°C to 125°C	CDIP – J	5962-8768104VEA	UC1825J-SP
	LCCC – FK	5962-8768104V2A	UC1825FK-SP

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

⁽²⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



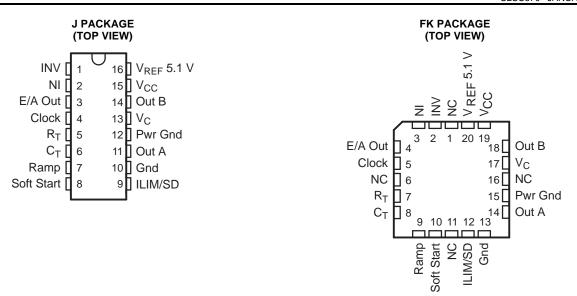


Table 1. TERMINAL FUNCTIONS

NAME	N	NO.				
NAME	J	FK	I/O	DESCRIPTION		
Clock	4	5	0	Output of the internal oscillator		
C _T	6	8	I	Timing capacitor connection pin for oscillator frequency programming. The timing capacitor should be connected to the device ground using minimal trace length.		
E/A Out	3	4	0	Output of the error amplifier for compensation		
Gnd	10	13	-	Analog ground return pin		
ILIM/SD	9	12	Ι	Input to the current limit comparator and the shutdown comparator		
INV	1	2	Ι	Inverting input to the error amplifier		
NC		1, 6, 11, 16	-	No connection		
NI	2	3	Ι	Non-inverting input to the error amplifier		
Out A	11	14	0	High-current totem pole output A of the on-chip drive stage		
Out B	14	18	0	High-current totem pole output B of the on-chip drive stage		
Pwr Gnd	12	15	-	Ground return pin for the output driver stage		
Ramp	7	9	I	Non-inverting input to the PWM comparator with 1.25-V internal input offset. In voltage mode operation this serves as the input voltage feed-forward function by using the CT ramp. In peak current mode operation, this serves as the slope compensation input.		
R _T	5	7	Ι	Timing resistor connection pin for oscillator frequency programming		
Soft Start	8	10	Ι	Soft-start input pin which also doubles as the maximum duty cycle clamp		
V _C	13	17	-	Power supply pin for the output stage. This pin should be bypassed with a 0.1-μF monolithic ceramic low ESL capacitor with minimal trace lengths.		
V _{CC}	15	19	-	Power supply pin for the device. This pin should be bypassed with a 0.1-μF monolithic ceramic low ESL capacitor with minimal trace lengths.		
V _{REF} 5.1 V	16	20	0	5.1-V reference. For stability, the reference should be bypassed with a 0.1-μF monolithic ceramic low ESL capacitor and minimal trace length to the ground plane.		



ABSOLUTE MAXIMUM RATINGS(1)

			UNIT
Supply voltage	V _C , V _{CC}	30	V
Output gurrant gourge or sink Out A Out B	DC	0.5	٨
Output current, source or sink, Out A, Out B	Pulse (0.5 μs)	2.0	Α
Analanianuta	INV, NI, Ramp	-0.3 to 7	V
Analog inputs	Soft Start, ILIM/SD	-0.3 to 6	V
Clock output current	Clock	-5	
Error amplifier output current	E/A Out	5	mA
Soft-start sink current	Soft Start	20	MA
Oscillator charging current	R _T	-5	
Power dissipation		1	W
Storage temperature range		-65 to 150	°C
Lead temperature (soldering, 10 seconds)		300	

⁽¹⁾ All voltages are with respect to GND; all currents are positive into, negative out of part; pin numbers refer to DIL-16 package.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range ($T_A = T_J = -55^{\circ}C$ to 125°C), unless otherwise noted.

		MIN	MAX	UNIT
V_{CC}	Supply voltage	10	30	V
	Sink/source output current (continuous or time average)	0	100	mA
	Reference load current	0	10	mA

THERMAL RATINGS TABLE

PACKAGE	θ _{JA} (° C/W)	^θ Jc (°C/W)
DIL-16 (J)	80–120	28 ⁽¹⁾
LCC-20 (FK)	70–80	20 ⁽¹⁾

⁽¹⁾ θ_{JC} data values stated were derived from MIL-STD-1835B. MIL-STD-1835B states that the baseline values shown are worst case (mean + 2s) for a 60 x 60 mil microcircit device silicon die and applicable for devices with die sizes up to 14400 square mils. For device die sizes greater than 14400 square mils use the following values; dual-in-line, 11°C/W; flat pack 10°C/W; pin grid array, 10°C/W.



ELECTRICAL CHARACTERISTICS

Unless otherwise stated, these specifications apply for R_T = 3.65 k Ω , C_T = 1 nF, V_{CC} = 15 V, -55°C < T_A < 125°C, T_A = T_J

$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ine regulation 10 $\lor \lor_{C_Q} < 30 \lor $	REFERENCE	,				
1 mA < l ₀ < 10 mA 5 20 mV cotal output variation Line, load, temperature 5.0 5.2 V μV thort-circuit current V _{REF} = 0 V -15 -50 -100 mA SCILLATOR SECTION Titled accuracy T ₃ = 25°C 360 400 440 kHz 400 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440 440	Output voltage	$T_J = 25^{\circ}C, I_O = 1 \text{ mA}$	5.05	5.10	5.15	V
Line, load, temperature 5.0 5.2 V Dutput noise voltage 10 Hz < f < 10 Hz 50 100 mV MFE 50	Line regulation	10 V < V _{CC} < 30 V		2	20	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Load regulation	1 mA < I _O < 10 mA		5	20	mV
Securation Variety V	Total output variation	Line, load, temperature	5.0		5.2	V
SECILLATOR SECTION T _J = 25°C 360 400 440 kHz	Output noise voltage	10 Hz < f < 10 kHz		50		μV
thical accuracy $T_J = 25^{\circ}C$ 360 400 440 kHz voltage stability 10 V < V _{CC} < 30 V 0.2% 2% 2% 26 voltage stability 10 V < V _{CC} < 30 V 0.2% 2% 26 voltage stability 10 V < V _{CC} < 30 V 0.2% 2% 26 voltage stability 10 V < V _{CC} < 30 V 0.2% 2% 26 voltage 10 V 2.3 2.9 V 2.5 voltage voltage 10 V 2.3 2.9 V 2.5 voltage 10 V 2.6 voltage 10 V 2.6 0.2 8 3.0 V 2.6 voltage 10 V 2.7 0.5	Short-circuit current	V _{REF} = 0 V	-15	-50	-100	mA
10 V < V _{CC} < 30 V	OSCILLATOR SECTION					
TMIN < TA < TMAX SW SW	Initial accuracy	T _J = 25°C	360	400	440	kHz
Line, Temperature 340 460 kHz	Voltage stability	10 V < V _{CC} < 30 V		0.2%	2%	
Standard	Temperature stability	$T_{MIN} < T_A < T_{MAX}$		5%		
2.3 2.9 V 2.5 2.6 2.8 3.0 V 2.5 2.5 2.9 V 2.5 2.5 2.5 3.0 V 2.5 2.5 2.5 3.0 V 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5 2.5	Total variation	Line, Temperature	340		460	kHz
2.6 2.8 3.0 V 2.5	Clock out high		3.9	4.5		V
1.0 1.25 V V V V V V V V V	Clock out low			2.3	2.9	V
1.6 1.8 2.1 V	Ramp peak ⁽¹⁾		2.6	2.8	3.0	V
### RROR AMPLIFIER ### opt offset voltage ### opt offset voltage ### opt offset current ### open-loop gain ### open-loop	Ramp valley ⁽¹⁾		0.7	1.0	1.25	V
Depart offset voltage 10 mV 1 mput bias current 10 mV 1 mput bias current 10 mV 1 mput offset current 10 mV 1 mput offset current 10 mV 1 mput offset current 10 mput offse	Ramp valley to peak ⁽¹⁾		1.6	1.8	2.1	V
Popul bias current	ERROR AMPLIFIER				•	
Depart offset current Dep	Input offset voltage				10	mV
Depen-loop gain	Input bias current			0.6	3	μΑ
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Input offset current			0.1	1	μΑ
SSRR $10 \text{ V} \times \text{V}_{\text{CC}} < 30 \text{ V}$ 85 110 dB Output sink current $V_{E/AOut} = 1 \text{ V}$ 1 2.5 mA Output source current $V_{E/AOut} = 4 \text{ V}$ -0.5 -1.3 mA Output high voltage $I_{E/AOut} = -0.5 \text{ mA}$ 4.0 4.7 5.0 V Output low voltage $I_{E/AOut} = 1 \text{ mA}$ 0 0.5 1.0 V Sain bandwidth product ⁽¹⁾ $f = 200 \text{ kHz}$ 5 10.5 MHz Siew rate ⁽¹⁾ 4 9 V/μ s WM COMPARATOR Bamp bias current $V_{Ramp} = 0 \text{ V}$ -1 -5 μ A Output y cycle range 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	Open-loop gain	1 V < V _O < 4 V	60	95		dB
Dutput sink current V _{E/AOut} = 1 V 1 2.5 mA Dutput source current V _{E/AOut} = 4 V -0.5 -1.3 mA Dutput light voltage I _{E/AOut} = -0.5 mA 4.0 4.7 5.0 V Dutput low voltage I _{E/AOut} = 1 mA 0 0.5 1.0 V Sain bandwidth product ⁽¹⁾ f = 200 kHz 5 10.5 MHz Siew rate ⁽¹⁾ a 9 V/μs VMM COMPARATOR -1 -5 μA Vamp bias current V _{Ramp} = 0 V -1 -5 μA Voluy cycle range 0% 80% -1 -5 μA Valuy cycle range 0% 1.1 1.25 V Valuy cycle range 0% 80% -1 -5 μA Valuy cycle range 0% 1.1 1.25 V Velay to output (1) 50 80 ns SOFT-START 3 9 20 μA Valuy cycle range	CMRR	$1.5 \text{ V} < \text{V}_{\text{CM}} < 5.5 \text{ V}$	75	95		dB
Dutput source current $V_{E/AOut} = 4 \text{ V}$ -0.5 -1.3 mA Dutput high voltage $I_{E/AOut} = -0.5 \text{ mA}$ 4.0 4.7 5.0 V Dutput low voltage $I_{E/AOut} = 1 \text{ mA}$ 0 0.5 1.0 V Bain bandwidth product ⁽¹⁾ $f = 200 \text{ kHz}$ 5 10.5 MHz Siew rate ⁽¹⁾ 4 9 $V/\mu s$ PWM COMPARATOR 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	PSRR	10 V < V _{CC} < 30 V	85	110		dB
Dutput high voltage $I_{E/AOut} = -0.5 \text{ mA}$ 4.0 4.7 5.0 V Dutput low voltage $I_{E/AOut} = 1 \text{ mA}$ 0 0.5 1.0 V Sain bandwidth product (1) $f = 200 \text{ kHz}$ 5 10.5 MHz Siew rate (1) 4 9 V/μ s VWM COMPARATOR V Samp bias current $V_{Ramp} = 0 \text{ V}$ -1 -5 μ A Duty cycle range 0% 80% 80% 80% 80% 80% 80% 80% 80% 9 80 ns 80% 9 80 ns 80% 80% 9 80 ns 80% 9 80% 9	Output sink current	V _{E/AOut} = 1 V	1	2.5		mA
Lincoln Lin	Output source current	$V_{E/AOut} = 4 V$	-0.5	-1.3		mA
Each bandwidth product $^{(1)}$ $f = 200 \text{ kHz}$ $f = 200 kHz$	Output high voltage	$I_{E/AOut} = -0.5 \text{ mA}$	4.0	4.7	5.0	V
Selew rate (1) 4 9 V/μs	Output low voltage	$I_{E/AOut} = 1 \text{ mA}$	0	0.5	1.0	V
PWM COMPARATOR Ramp bias current $V_{Ramp} = 0 \text{ V}$ -1 -5 μA Puty cycle range 0% 80% E/A out zero dc threshold $V_{Ramp} = 0 \text{ V}$ 1.1 1.25 V Pelay to output ⁽¹⁾ 50 80 ns E/Arge current $V_{Soft Start} = 0.5 \text{ V}$ 3 9 20 μA Pischarge current $V_{Soft Start} = 1 \text{ V}$ 1 1 1 1 1 1 1 1 1 1	Gain bandwidth product (1)	f = 200 kHz	5	10.5		MHz
Ramp bias current $V_{Ramp} = 0 \text{ V}$ -1 -5 μA buty cycle range 0% 0% 80% 0% 0% 0% 0% 0% 0% 0%	Slew rate ⁽¹⁾		4	9		V/μs
The policy cycle range 0% and 0% a	PWM COMPARATOR					
$V_{Ramp} = 0 \ V$ $V_{Ramp} = 0 \ V$ $V_{Ramp} = 0 \ V$ $V_{Soft Start} = 0.5 \ V$ $V_{Soft Start} = 0.5 \ V$ $V_{Soft Start} = 1 \ V$ $V_{Soft $	Ramp bias current	$V_{Ramp} = 0 V$		-1		μΑ
Delay to output $^{(1)}$ 50 80 ns $^{(1)}$ 50 80 ns $^{(2)}$ 50 80 ns $^{(3)}$ 50 80 ns $^{(3)}$ 50 80 ns $^{(3)}$ 50 80 ns $^{(3)}$ 50 80 ns $^{(4)}$ 60 80 90 90 90 90 90 90 90 9	Duty cycle range		0%		80%	
Charge current $V_{Soft\ Start}=0.5\ V$ 3 9 20 μA Discharge current $V_{Soft\ Start}=1\ V$ 1 mA CURRENT LIMIT/SHUTDOWN Current limit/shutdown bias current $0 < V_{ILIM/SD} < 4\ V$ 15 μA Current limit threshold 0.9 1.0 1.1 V Shutdown threshold	E/A out zero dc threshold	$V_{Ramp} = 0 V$	1.1	1.25		V
Charge current $V_{Soft\ Start} = 0.5\ V$ 3 9 20 μA Discharge current $V_{Soft\ Start} = 1\ V$ 1 mA CURRENT LIMIT/SHUTDOWN Current limit/shutdown bias current $0 < V_{ILIM/SD} < 4\ V$ 15 μA Current limit threshold 0.9 1.0 1.1 V Shutdown threshold 1.25 1.40 1.55 V	Delay to output ⁽¹⁾			50	80	ns
Discharge current $V_{Soft\ Start}=1\ V$ 1 mA Current limit/shutdown bias current $0 < V_{ILIM/SD} < 4\ V$ 15 μ A Current limit threshold 0.9 1.0 1.1 V shutdown threshold 1.25 1.40 1.55 V	SOFT-START					
CURRENT LIMIT/SHUTDOWN Current limit/shutdown bias current 0 < V _{ILIM/SD} < 4 V	Charge current	V _{Soft Start} = 0.5 V	3	9	20	μΑ
Current limit/shutdown bias current $0 < V_{ILIM/SD} < 4 \text{ V}$ 15 μ A Current limit threshold 0.9 1.0 1.1 V Shutdown threshold 1.25 1.40 1.55 V	Discharge current	V _{Soft Start} = 1 V	1			mA
Current limit threshold 0.9 1.0 1.1 V Shutdown threshold 1.25 1.40 1.55 V	CURRENT LIMIT/SHUTDOWN					
Shutdown threshold 1.25 1.40 1.55 V	Current limit/shutdown bias current	0 < V _{ILIM/SD} < 4 V			15	μΑ
	Current limit threshold		0.9	1.0	1.1	V
Delay to output ⁽¹⁾ 50 80 ns	Shutdown threshold		1.25	1.40	1.55	V
	Delay to output ⁽¹⁾			50	80	ns

⁽¹⁾ Parameters ensured by design and/or characterization, if not production tested.



ELECTRICAL CHARACTERISTICS (continued)

Unless otherwise stated, these specifications apply for $R_T = 3.65 \text{ k}\Omega$, $C_T = 1 \text{ nF}$, $V_{CC} = 15 \text{ V}$, $-55^{\circ}\text{C} < T_A < 125^{\circ}\text{C}$, $T_A = T_J$

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OUTPUT					
Low level output valtage	I _{OUT} = 20 mA		0.25	0.40	V
Low-level output voltage	I _{OUT} = 200 mA		1.2	2.2	V
High-level output voltage	$I_{OUT} = -20 \text{ mA}$	13.0	13.5		V
riigii-ievei output voitage	$I_{OUT} = -200 \text{ mA}$	12.0	13.0		V
Collector leakage	V _C = 30 V		10	500	μΑ
Rise/fall time (2)	C _L = 1 nF		30	75	ns
UNDER-VOLTAGE LOCKOUT					
Start threshold		8.8	9.2	9.6	V
UVLO hysteresis		0.4	8.0	1.2	V
SUPPLY CURRENT SECTION					
Startup current	V _{CC} = 8 V		1.1	2.5	mA
I _{cc}	$V_{INV} = V_{Ramp} = V_{ILIM/SD} = 0 V, V_{NI} = 1 V$		22	33	mA

⁽²⁾ Parameters ensured by design and/or characterization, if not production tested.



PRINTED CIRCUIT BOARD LAYOUT CONSIDERATIONS

High speed circuits demand careful attention to layout and component placement. To ensure proper performance of the UC1825 follow these rules:

- 1. Use a ground plane.
- 2. Damp or clamp parasitic inductive kick energy from the gate of driven MOSFETs. Do not allow the output pins to ring below ground. A series gate resistor or a shunt 1-A Schottky diode at the output pin serves this purpose.
- 3. Bypass V_{CC} , V_{C} , and V_{REF} . Use 0.1- μ F monolithic ceramic capacitors with low equivalent series inductance. Allow less than 1-cm of total lead length for each capacitor between the bypassed pin and the ground plane.
- 4. Treat the timing capacitor, C_T, like a bypass capacitor.

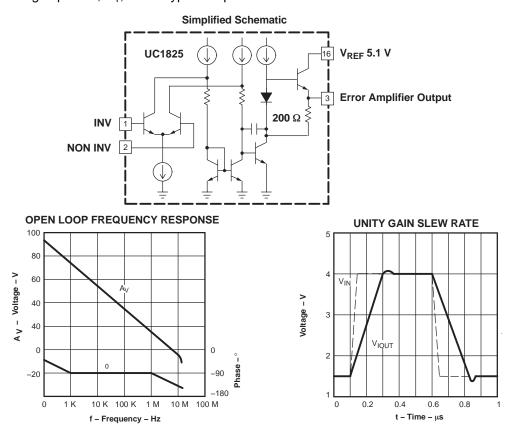
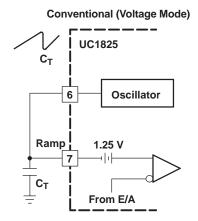
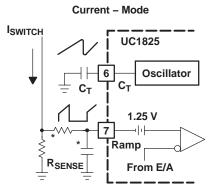


Figure 1. Error Amplifier







* A small filter may be required to suppress switch noise.

Figure 2. PWM Applications

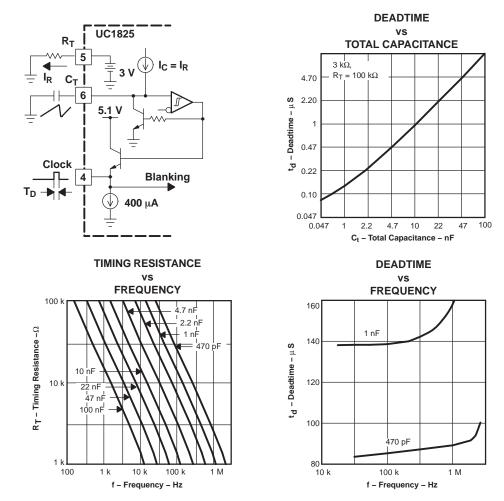


Figure 3. Oscillator Circuit

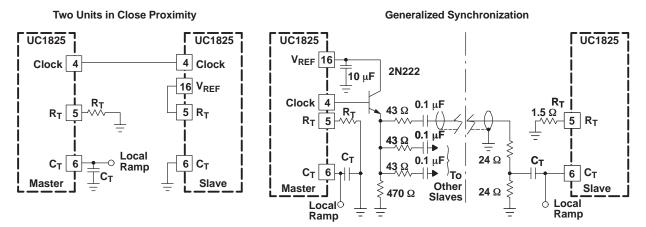


Figure 4. Synchronized Operation

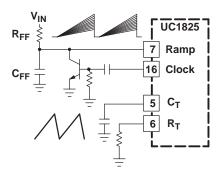


Figure 5. Forward Technique for Off-Line Voltage Mode Application

The circuit shown in Figure 5 will achieve a constant volt-second product clamp over varying input voltages. The ramp generator components, R_T and C_R are chosen so that the ramp at the ILIM/SD pin crosses the 1-V threshold at the same time the desired maximum volt-second product is reached. The delay through the functional nor block must be such that the ramp capacitor can be completely discharged during the minimum deadtime.

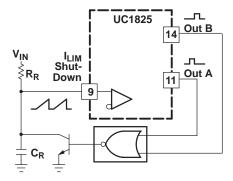


Figure 6. Constant Volt-Second Clamp Circuit

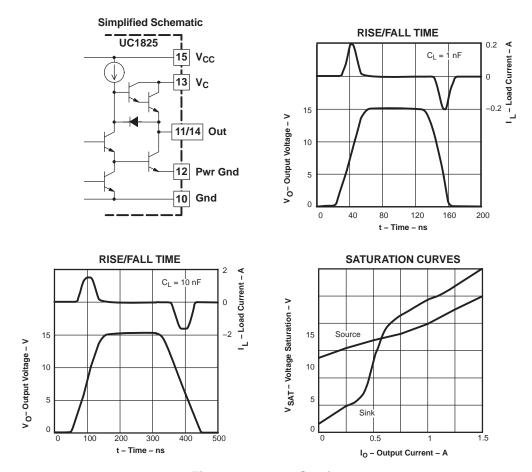


Figure 7. Output Section

The circuit in Figure 7 is useful for exercising many of the UC1825 functions and measuring their specifications.

As with any wideband circuit, careful grounding and bypass procedures should be followed. The use of a ground plane is highly recommended.

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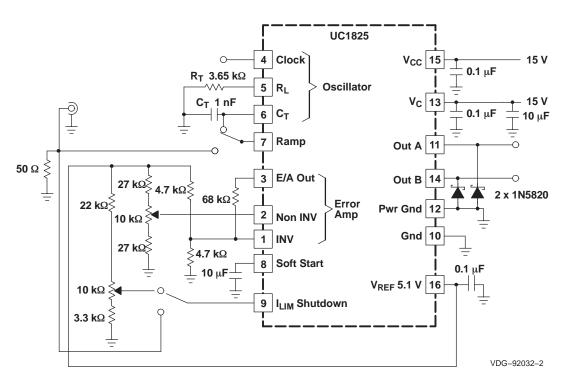


Figure 8. Open-Loop Laboratory Test Fixture



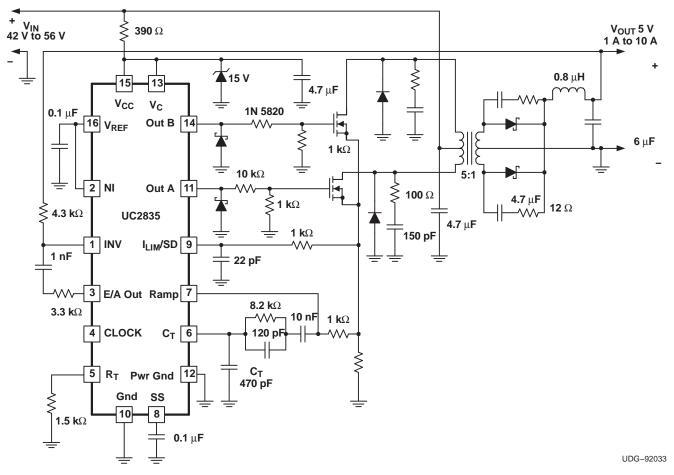


Figure 9. Design Example: 50 W, 48-V to 5-V DC-to-DC Converter – 1.5-MHz Clock Frequency



PACKAGE OPTION ADDENDUM

28-May-2009 www ti com

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
5962-8768101V2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-8768101VEA	ACTIVE	CDIP	J	16	1	TBD	A42	N / A for Pkg Type
5962-8768104V2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-8768104VEA	ACTIVE	CDIP	J	16	1	TBD	A42	N / A for Pkg Type

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL. Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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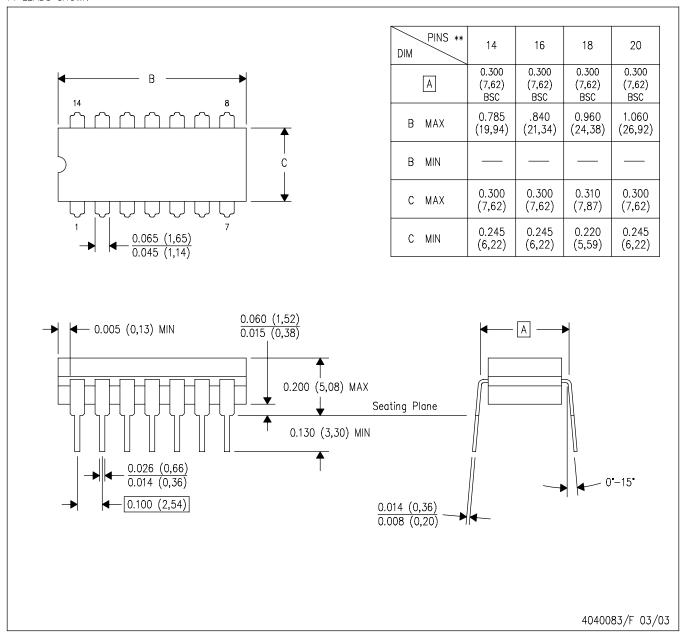
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF UC1825-SP:

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

14 LEADS SHOWN



NOTES:

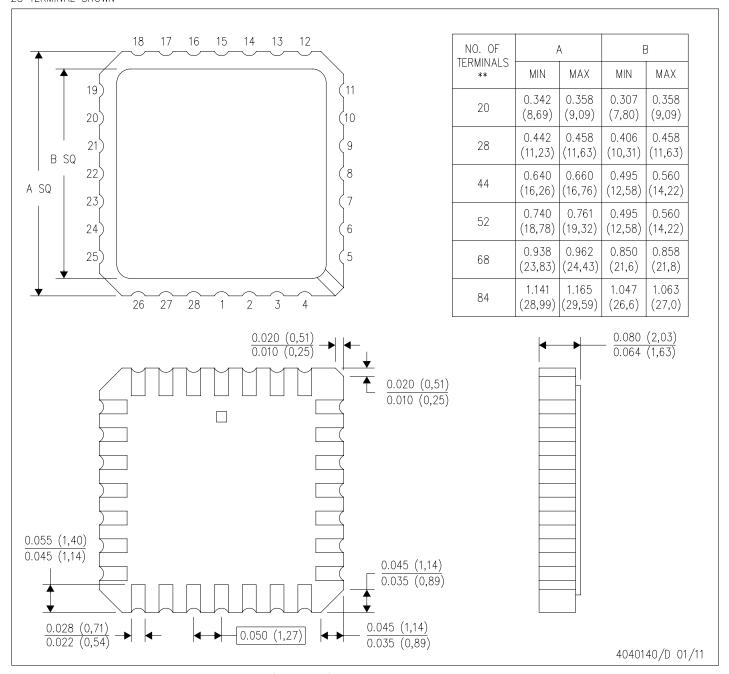
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

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FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004

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